Part Number	Customer

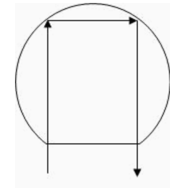
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	WaferVendor
	2.0	Primary Flat Orientation	<110> +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	Wafer Vendor
	5.0	Overall Thickness	406.00 +/- 17.00 um	Guaranteed by Process
	6.0	Total Thickness Variation (TTV)	<5.00um	Guaranteed by Process
	7.0	Bow	<60.00um	Guaranteed by Process
	8.0	Warp	<60.00um	Guaranteed by Process
	9.0	Edge Exclusion	5 mm	Guaranteed by Process
HandleSilicon	10.0	Handle Growth Method	CZ	Wafer Vendor
	11.0	Handle Orientation	<100> +/- 0.5 degree	Wafer Vendor
	12.0	Handle Carbon Concentration	<2e16 at/cm3	Wafer Vendor
	13.0	Handle Oxygen Concentration	<1e18 at/cm3	Wafer Vendor
	14.0	Handle Thickness	342.00 +/- 15.00 um	Guaranteed by Process
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Boron	Wafer Vendor
	17.0	Handle Resistivity	< 0.005 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Lapped and etched with no oxide and lasermark	Wafer Vendor
DeviceSilicon	19.0	Device Growth Method	FZ	Customer Supplied
	20.0	Device Orientation	<100> +/- 0.5 degree	Customer Supplied
	21.0	Nominal Thickness	58.00 +/- 2.00 um	FTIR, 100% 9-Pt (note3)
	22.0	Distance to device silicon edge from wafer edge	<= 2mm	Guaranteed by Process
	23.0	Device Doping Type	P	Customer Supplied
	24.0	Device Dopant	Boron	Customer Supplied
	25.0	Device Resistivity	1000-2000 Ohmcm	Customer Supplied
	26.0	Buried Layer Implant	none	Implant Vendor
	27.0	Voids	none	Guaranteed by Process, SAM inspection
	28.0	Haze	none	Guaranteed by Process, Bright LIght inspection
	29.0	Scratches	none	Guaranteed by Process, Bright LIght inspection

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

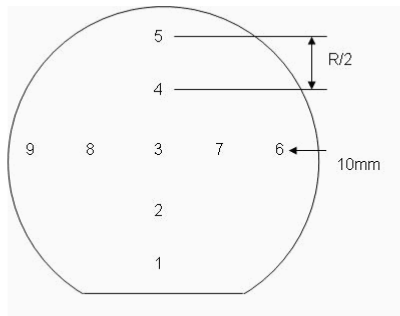
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information